Noninverting Buffer / CMOS Logic Level Shifter

with LSTTL-Compatible Inputs

The MC74VHC1GT126 is a single gate noninverting 3–state buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC1GT126 requires the 3–state control input (\overline{OE}) to be set Low to place the output into the high impedance state.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT126 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GT126 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC}=0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: tpD = 3.5 ns (Typ) at VCC = 5 V
- Low Power Dissipation: $I_{CC} = 1 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- CMOS–Compatible Outputs: V_{OH} > 0.8 V_{CC}; V_{OL} < 0.1 V_{CC} @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16

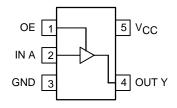


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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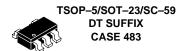
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MARKING DIAGRAMS





Pin 1 d = Date Code





Pin 1 d = Date Code

PIN ASSIGNMENT						
1	OE					
2	IN A					
3	GND					
4	OUT Y					
5	Vcc					

FUNCTION TABLE

A Input	OE Input	Y Output
L	Н	L
Н	н	Н
X	L	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS (Note 1)

Symbol	Characteristics	Value	Unit
VCC	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
Vout	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
lK	Input Diode Current	-20	mA
lok	Output Diode Current VOUT < GND; VOUT > VCC	+20	mA
lout	DC Output Current, per Pin	+25	mA
Icc	DC Supply Current, V _{CC} and GND	+50	mA
P_{D}	Power dissipation in still air SC–88A, TSOP–5	200	mW
θ JA	Thermal resistance SC–88A, TSOP–5	333	°C/W
TL	Lead temperature, 1 mm from case for 10 s	260	°C
TJ	Junction temperature under bias	+150	°C
T _{stg}	Storage temperature	-65 to +150	°C
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{Latch} -Up	Latch–Up Performance Above V _{CC} and Below GND at 125°C (Note 5)	±500	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those
indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional
operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
VCC	DC Supply Voltage	3.0	5.5	V	
VIN	DC Input Voltage		0.0	5.5	V
VOUT	DC Output Voltage		0.0	VCC	V
TA	Operating Temperature Range		- 55	+125	°C
t _r , t _f	Input Rise and Fall Time V _{CC}	= 5.0 V ± 0.5 V	0	20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

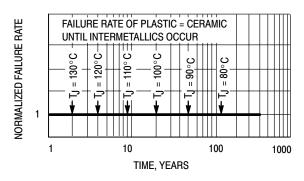


Figure 3. Failure Rate vs. Time Junction Temperature

^{2.} Tested to EIA/JESD22-A114-A

^{3.} Tested to EIA/JESD22-A115-A

^{4.} Tested to JESD22-C101-A

^{5.} Tested to EIA/JESD78

DC ELECTRICAL CHARACTERISTICS

			vcc	Т	T _A = 25°	С	T _A ≤	85°C	-55 ≤ T _A	√ ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
VOH	Minimum High-Level Output	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
VOL	Low-Level Output	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	Voltage V _{IN} = V _{IH} or V _{IL}	VIN = VIH or VIL IOL = 4 mA IOL = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μА
lcc	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1.0		20		40	μΑ
ICCT	Quiescent Supply Current	Input: V _{IN} = 3.4 V Other Input: V _{CC} or GND	5.5			1.35		1.50		1.65	mA
l _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μА
loz	Maximum 3–State Leakage Current	V _{IN} = V _{IH} or V _{IL}	5.5			± 0.25		± 2.5		± 2.5	μА

AC ELECTRICAL CHARACTERISTICS Input $t_{\mbox{\scriptsize f}} = t_{\mbox{\scriptsize f}} = 3.0 \ \mbox{ns}$

				T _A = 25°		5°C T _A ≤ 85°C		$-55 \le T_A \le 125$ °C			
Symbol	Parameter	Test Condit	ions	Min	Тур	Max	Min	Max	Min	Max	Unit
tPLH, tPHL	Maximum Propagation Delay, A to Y	V _{CC} = 3.3 ± 0.3 V	C _L = 15pF C _L = 50pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
	(Figure 3. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
tPZL, tPZH	Maximum Output Enable TIme, OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = R_I = 500 \Omega$			5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
	(Figure 4. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = R_I = 500 \Omega$			3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t _{PLZ} , t _{PHZ}	Maximum Output Disable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = R_I = 500 \Omega$	_		6.5 8.0	9.7 13.2	1.0 1.0	11.5 15.0		14.5 18.0	ns
	(Figure 4. and 5.)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = R_I = 500 \Omega$			4.8 7.0	6.8 8.8	1.0 1.0	8.0 10.0		10.0 12.0	
C _{in}	Maximum Input Capacitance				4	10		10		10	pF
C _{out}	Maximum Three—State Output Capacitance (Output in High Impedance State)				6						pF
			т.	nical @	25°C \	/oo = 5 0 \	,				

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 6)	14	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

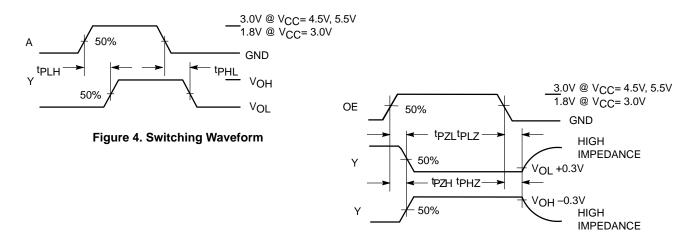
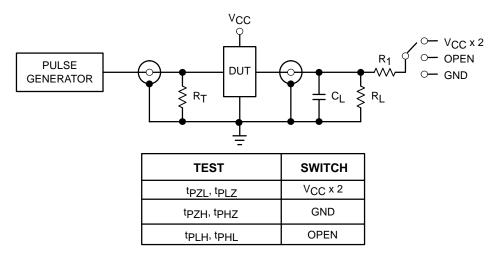


Figure 5. Switching Waveform



C_L = 50 pF equivalent (Includes jig and probe capacitance) or 15 pF R_L = R₁ = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

DEVICE ORDERING INFORMATION

	Device Nomenclature							
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
MC74VHC1GT126DF1	МС	74	VHC1G	T126	DF	1	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1GT126DF2	МС	74	VHC1G	T126	DF	2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1GT126DT1	МС	74	VHC1G	T126	DT	1	TSOP5 / SOT-23 / SC-59	178 mm (7") 3000 Unit

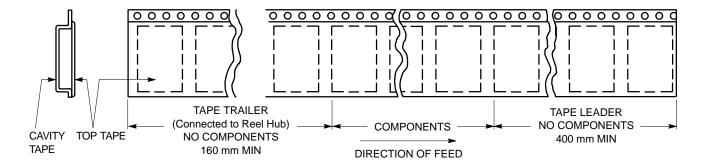


Figure 7. Tape Ends for Finished Goods

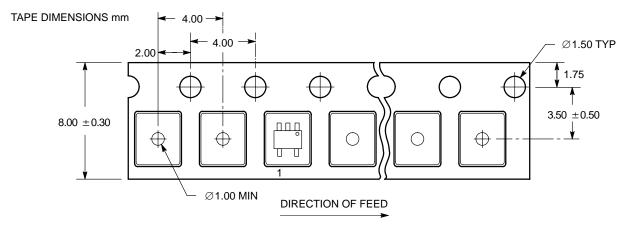


Figure 8. SC-70-5/SC-88A/SOT-353 DF1 Reel Configuration/Orientation

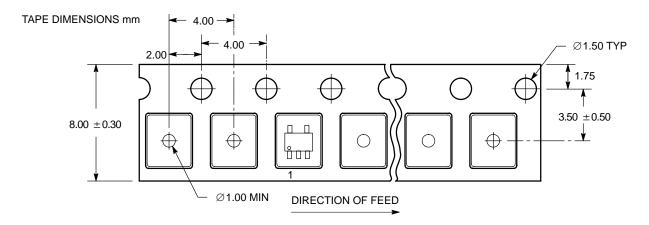


Figure 9. SC-70/SC-88A/SOT-353 DF2 and SOT23-5/TSOP-5/SC59-5 DT1 Reel Configuration/Orientation

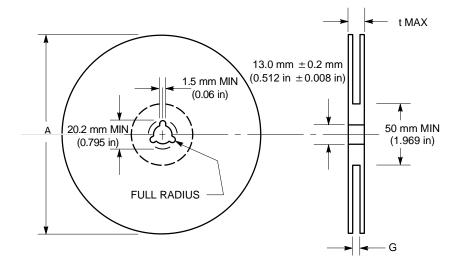


Figure 10. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	1, 2	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

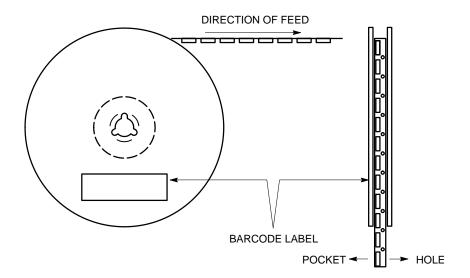
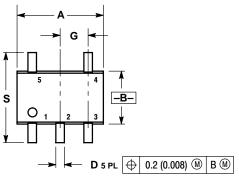


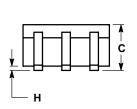
Figure 11. Reel Winding Direction

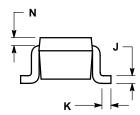
PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70 **DF SUFFIX**

5-LEAD PACKAGE CASE 419A-02 ISSUE F

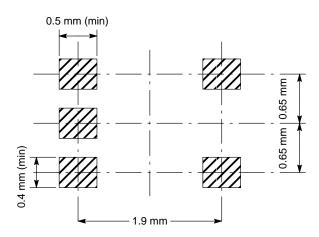






- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.

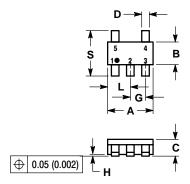
	INC	HES	MILLIM	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
H		0.004	-	0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	

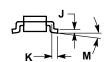


PACKAGE DIMENSIONS

TSOP-5 / SOT-23 / SC-59 **DT SUFFIX**

5-LEAD PACKAGE CASE 483-01 **ISSUE A**

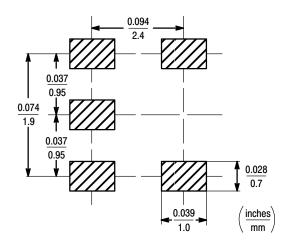




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0 °	10°	0°	10°
S	2.50	3.00	0.0985	0.1181



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